



2SK1056, 2SK1057, 2SK1058

Silicon N Channel MOS FET

REJ03G0906-0200
(Previous: ADE-208-1244)
Rev.2.00
Sep 07, 2005

Application

Low frequency power amplifier

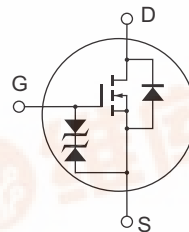
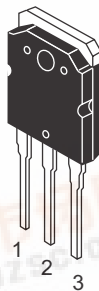
Complementary pair with 2SJ160, 2SJ161 and 2SJ162

Features

- Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier

Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)



1. Gate
2. Source (Flange)
3. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1056	V_{DSX}	120	V
	2SK1057		140	
	2SK1058		160	
Gate to source voltage		V_{GSS}	± 15	V
Drain current		I_D	7	A
Body to drain diode reverse drain current		I_{DR}	7	A
Channel dissipation		P_{ch}^{*1}	100	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics

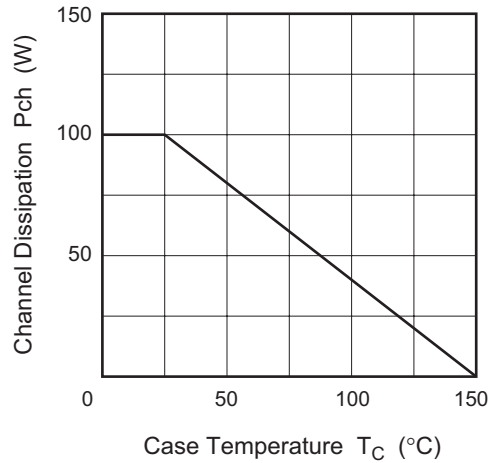
(Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1056	$V_{(BR)DSX}$	120	—	—	V	$I_D = 10\text{ mA}$, $V_{GS} = -10\text{ V}$
	2SK1057		140				
	2SK1058		160				
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	0.15	—	1.45	V	$I_D = 100\text{ mA}$, $V_{DS} = 10\text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	12	V	$I_D = 7\text{ A}$, $V_{GD} = 0^{*2}$
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = 3\text{ A}$, $V_{DS} = 10\text{ V}^{*2}$
Input capacitance		C_{iss}	—	600	—	pF	$V_{GS} = -5\text{ V}$, $V_{DS} = 10\text{ V}$, $f = 1\text{ MHz}$
Output capacitance		C_{oss}	—	350	—	pF	
Reverse transfer capacitance		C_{rss}	—	10	—	pF	
Turn-on time		t_{on}	—	180	—	ns	$V_{DD} = 20\text{ V}$, $I_D = 4\text{ A}$
Turn-off time		t_{off}	—	60	—	ns	

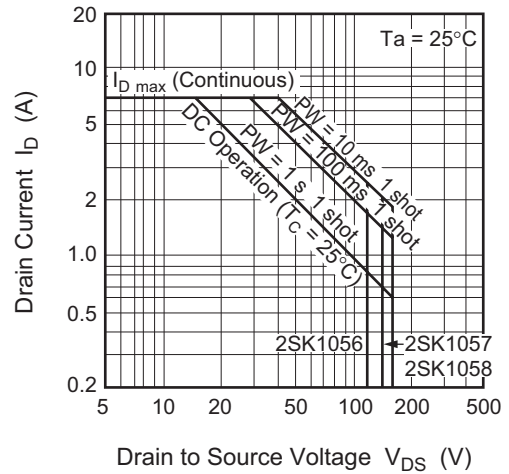
Note: 2. Pulse test

Main Characteristics

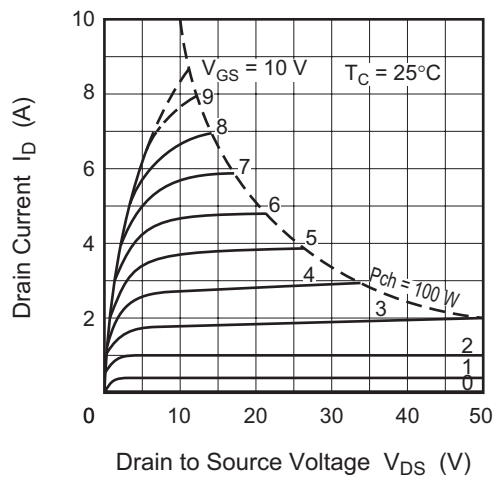
Power vs. Temperature Derating



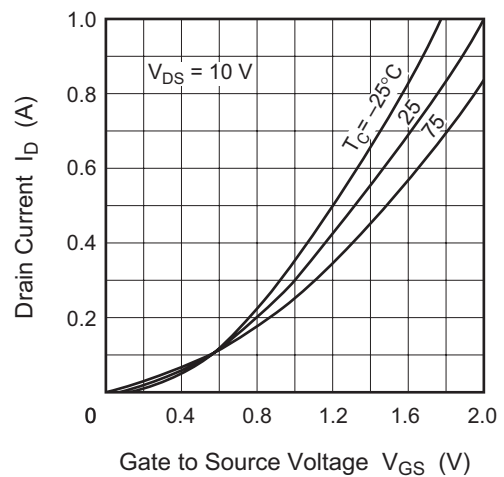
Maximum Safe Operation Area



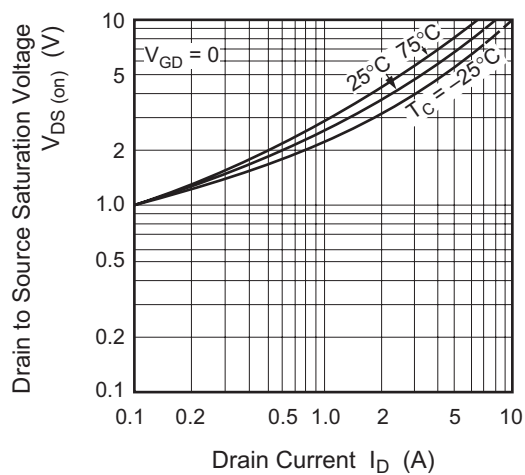
Typical Output Characteristics



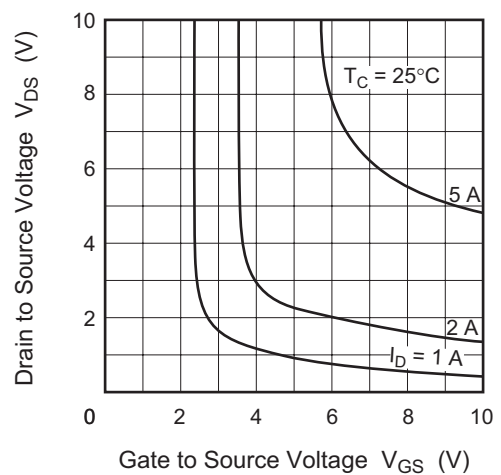
Typical Transfer Characteristics

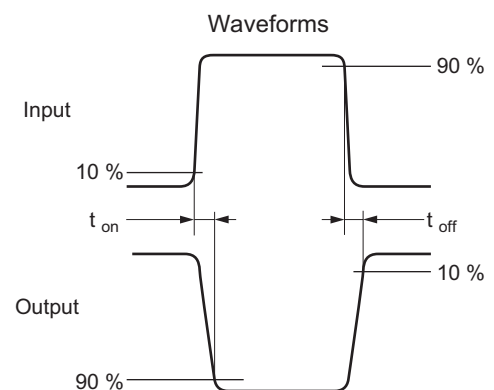
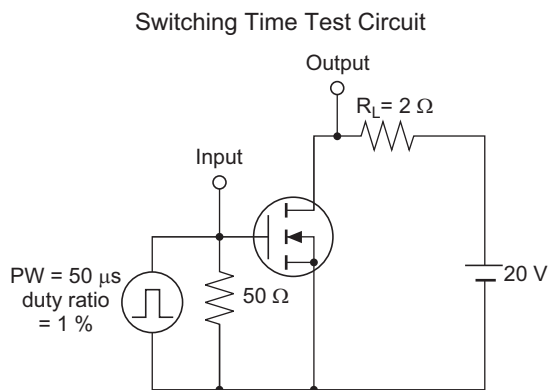
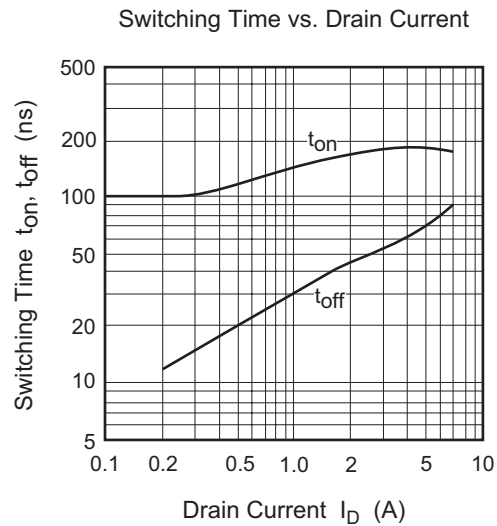
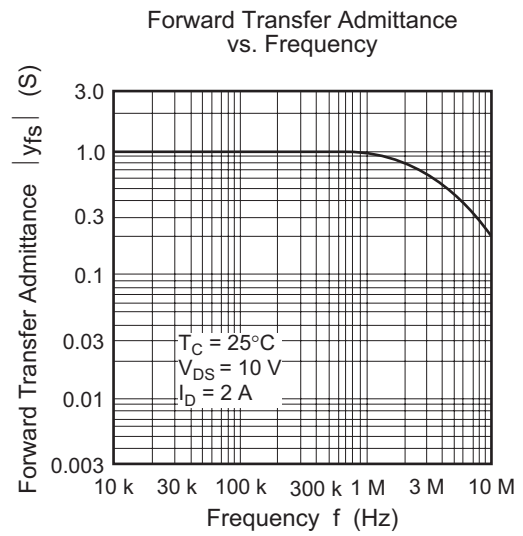
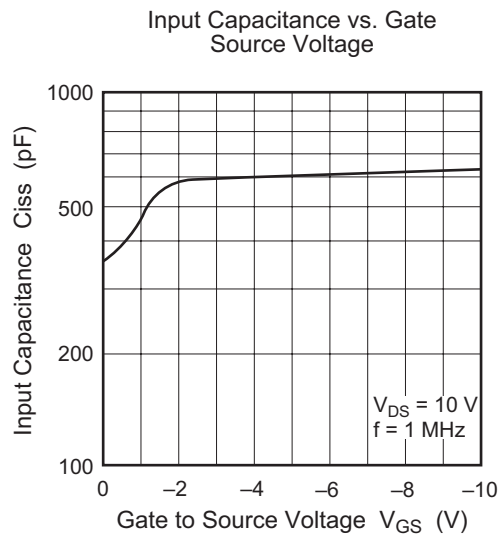


Drain to Source Saturation Voltage vs. Drain Current

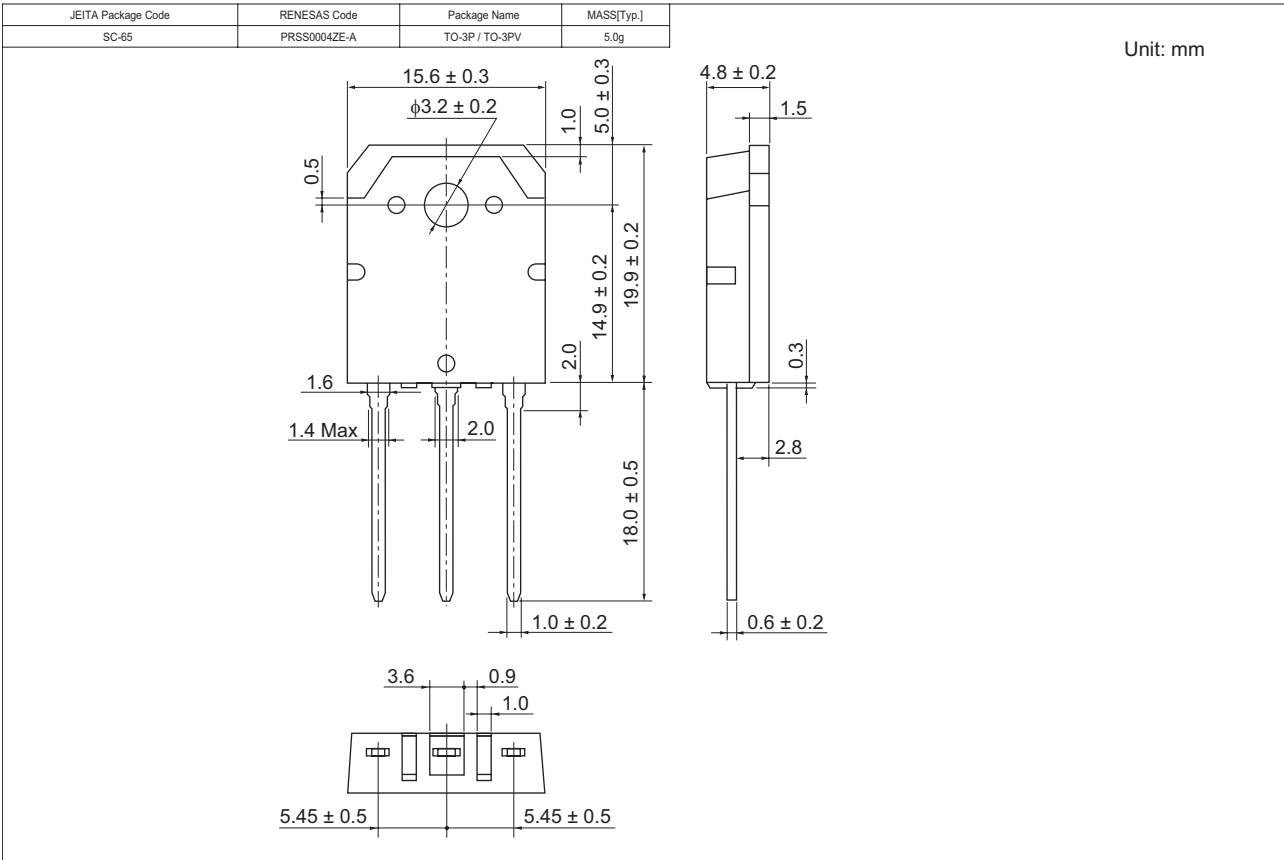


Drain to Source Voltage vs. Gate to Source Voltage





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1056-E	360 pcs	Box (Tube)
2SK1057-E	360 pcs	Box (Tube)
2SK1058-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510